

ABSTRACT

1 Heat is applied to a conductive structure that includes
2 one or more vias, and the temperature at or near the point of
3 heat application is measured. The measured temperature
4 indicates the integrity or the defectiveness of various features
5 (e.g. vias and/or traces) in the conductive structure, near the
6 point of heat application. Specifically, a higher temperature
7 measurement (as compared to a measurement in a reference
8 structure) indicates a reduced heat transfer from the point of
9 heat application, and therefore indicates a defect. The
10 reference structure can be in the same die as the conductive
11 structure (e.g. to provide a baseline) or outside the die but in
12 the same wafer (e.g. in a test structure) or outside the wafer
13 (e.g. in a reference wafer), depending on the embodiment.